

9/2/2016

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900376352 08/29/2016

**TRADEMARK ASSIGNMENT COVER SHEET**

Electronic Version v1.1  
 Stylesheet Version v1.2

ETAS ID: TM396703

<b>SUBMISSION TYPE:</b>	NEW ASSIGNMENT
<b>NATURE OF CONVEYANCE:</b>	SECURITY INTEREST

**CONVEYING PARTY DATA**

Name	Formerly	Execution Date	Entity Type
Plasma-Therm, LLC		08/26/2016	Limited Liability Company: FLORIDA
Drytek, LLC		08/26/2016	Limited Liability Company: <del>FLORIDA</del> Delaware

**RECEIVING PARTY DATA**

<b>Name:</b>	SunTrust Bank
<b>Street Address:</b>	303 Peachtree Street
<b>Internal Address:</b>	Suite 3600
<b>City:</b>	Atlanta
<b>State/Country:</b>	GEORGIA
<b>Postal Code:</b>	30308
<b>Entity Type:</b>	Corporation: GEORGIA

9/2/16

**PROPERTY NUMBERS Total: 15**

Property Type	Number	Word Mark
Registration Number:	4818288	SINGULATOR
Registration Number:	4136245	CORTEX
Registration Number:	2893124	VERSALINE
Registration Number:	2893123	SHUTTLELINE
Registration Number:	3841335	VERSAWORKS
Registration Number:	3840760	PTI
Registration Number:	3730528	790+
Registration Number:	3806343	NEXTRAL
Registration Number:	3687253	PLASMA-THERM
Registration Number:	3902954	ENDPOINTWORKS
Registration Number:	3383876	MASK ETCHER
Registration Number:	2001901	VERSALOCK
Registration Number:	1625640	SHUTTLELOCK
Registration Number:	4210502	DRYTEK
Registration Number:	3994856	DRYTEK

OP \$390.00 4818288

**CORRESPONDENCE DATA**

Fax Number: 2026637271

*Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.*

Phone: 2026637271

Email: thomas.brooke@hkllaw.com, ptdocketing@hkllaw.com

Correspondent Name: Thomas W. Brooke

Address Line 1: 800 17th Street, NW

Address Line 2: Suite 1100

Address Line 4: Washington, D.C. 20006

<b>NAME OF SUBMITTER:</b>	Thomas W. Brooke
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<b>SIGNATURE:</b>	/Thomas W. Brooke/
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<b>DATE SIGNED:</b>	08/29/2016
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**Total Attachments: 15**

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## INTELLECTUAL PROPERTY SECURITY AGREEMENT

This INTELLECTUAL PROPERTY SECURITY AGREEMENT, dated as of August 26, 2016 (as amended, supplemented or otherwise modified from time to time, the "Intellectual Property Security Agreement"), is made by RAJE Technology Group, LLC, a Florida limited liability company ("RAJE"), Plasma-Therm, LLC, a Florida limited liability company ("Plasma"), Rev-Tech Manufacturing Solutions, LLC, a Florida limited liability company ("Rev-Tech"), Logix Technology Holdings, LLC, a Delaware limited liability company ("Logix"), Plasma-Therm IC-DISC, Inc., a Delaware corporation ("Plasma-IC DISC"), Drytek, LLC, a Delaware limited liability company ("Drytek") and Hine Automation, LLC, a Delaware Limited Liability Company ("Hine") (RAJE, Plasma, Rev-Tech, Logix, Plasma-IC DISC, Drytek and Hine are sometimes each hereafter referred to as a "Grantor" and collectively, the "Grantors") in favor of SunTrust Bank, a Georgia corporation (the "Lender").

WHEREAS, RAJE Technology Group, LLC, a Florida limited liability company ("RAJE"), and Plasma-Therm, LLC, a Florida limited liability company ("Plasma") (RAJE and Plasma, are sometimes referred to herein as each, a "Borrower" and collectively, the "Borrowers") have entered into that certain Loan and Security Agreement (Ex-Im Bank-Guaranteed Revolving Line of Credit), dated as of even date herewith (as amended, restated, supplemented or otherwise modified from time to time, the "Loan and Security Agreement"), by and among the Borrowers and the Lender. Capitalized terms used and not defined herein have the meanings given such terms in the Loan and Security Agreement.

WHEREAS, each Borrower pursuant to the terms and conditions of the Loan and Security Agreement has granted a security interest in all General Intangibles of such Borrower, including, but not limited to, all Intellectual Property (as defined below) for the benefit of the Lender.

WHEREAS, Rev-Tech, Logix, Plasma-IC-DISC, Drytek, and Hine Automation, LLC, a Delaware Limited Liability Company ("Hine") (Plasma, Rev-Tech, Logix, Plasma-IC DISC, Drytek and Hine are sometimes referred to herein as each, a "Guarantor" and collectively, the "Guarantors") have entered into that certain Security Agreement, dated as of even date herewith (as amended, restated, supplemented or otherwise modified from time to time, the "Security Agreement"), by and among the Guarantors and the Lender, to secure the prompt payment and performance of any and all obligations of the Borrowers.

WHEREAS, each Guarantor pursuant to the terms and conditions of the Security Agreement have granted a security interest in all General Intangibles of such Guarantor, including, but not limited to, all Intellectual Property (as defined below) for the benefit of the Lender.

WHEREAS, it is a condition precedent to the obligation of the Lender to make its extension of credit to the Borrowers under the Loan and Security Agreement that the Borrowers and Guarantors (collectively, the "Grantors") shall have each executed and delivered to and for the benefit of the Lender (i) the Loan and Security Agreement in the case of the Borrowers, and (ii) the Security Agreement in the case of the Guarantors (collectively, the "Security Agreements").

WHEREAS, under the terms of the Security Agreements, each Grantor has granted a security interest in certain Intellectual Property (as defined below) of such Grantor to and for the benefit of the Lender and has agreed as a condition thereof to execute this Intellectual Property Security Agreement for recording with the United States Patent and Trademark Office, the United States Copyright Office, and other applicable Governmental Authorities.

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, the Grantors agree as follows:

SECTION 1. Grant of Security. Each Grantor hereby grants to the Lender a security interest in and to all of such Grantor's right, title and interest in and to the following (the "Intellectual Property Collateral"), whether now existing or hereafter arising, as collateral security for the prompt and complete payment and performance when due (whether at the stated maturity, by acceleration or otherwise) of the Obligations:

(a) (i) all trademarks, service marks, trade names, corporate names, company names, business names, trade dress, trade styles, logos, or other indicia of origin or source identification, trademark and service mark registrations, and applications for trademark or service mark registrations and any new renewals thereof, including, without limitation, each registration and application identified in Schedule 1, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto, together in each case with the goodwill of the business connected with the use of, and symbolized by, each of the above (collectively, the "Trademarks");

(b) (i) all patents, patent applications and patentable inventions, including, without limitation, each issued patent and patent application identified in Schedule 1, (ii) all inventions and improvements described and claimed therein, (iii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iv) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (v) all reissues, divisions, continuations, continuations-in-part, substitutes, renewals, and extensions thereof, all improvements thereon and all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto (collectively, the "Patents");

(c) (i) all copyrights, whether or not the underlying works of authorship have been published, and all works of authorship and other intellectual property rights therein (including, but not limited to, business software), all copyrights of works based on, incorporated in, derived from or relating to works covered by such copyrights, all right, title and interest to make and exploit all derivative works based on or adopted from works covered by such copyrights, and all copyright registrations and copyright applications, and any renewals or extensions thereof, including, without limitation, each registration and application identified in Schedule 1, (ii) the rights to print, publish and distribute any of the foregoing, (iii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iv) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (v) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto ("Copyrights");

(d) (i) all trade secrets and all confidential and proprietary information, including know-how, manufacturing and production processes and techniques, inventions, research and development information, technical data, financial, marketing and business data, pricing and cost information, business and marketing plans, and customer and supplier lists and information, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations thereof, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any

kind whatsoever of such Grantor accruing thereunder or pertaining thereto (collectively, the "Trade Secrets");

(e) (i) all licenses or agreements, whether written or oral, providing for the grant by or to any Grantor of: (A) any right to use any Trademark or Trade Secret, (B) any right under any Patent, and (C) any right under any Copyright, (ii) the right to sue or otherwise recover for any and all past, present and future infringements and misappropriations of any of the foregoing, (iii) all income, royalties, damages and other payments now and hereafter due and/or payable with respect thereto (including, without limitation, payments under all licenses entered into in connection therewith, and damages and payments for past, present or future infringements thereof), and (iv) all other rights of any kind whatsoever of such Grantor accruing thereunder or pertaining thereto; and

(f) any and all proceeds of the foregoing.

SECTION 2. Recordation. Each Grantor authorizes and requests that the Register of Copyrights, the Commissioner of Patents and Trademarks and any other applicable government officer record this Intellectual Property Security Agreement.

SECTION 3. Execution in Counterparts. This Agreement may be executed in any number of counterparts (including by electronic transmission), each of which when so executed shall be deemed to be an original and all of which taken together shall constitute one and the same agreement.

SECTION 4. Governing Law. This Intellectual Property Security Agreement shall be governed by, and construed and interpreted in accordance with the laws of the State of Florida. Without limiting the applicability of any other provision of the Loan and Security Agreement, the terms of Section 11.1 (*Governing Law; Choice of Forum; Service of Process; Jury Trial Waiver*) of the Loan and Security Agreement in the case of the Borrowers, and the corresponding provisions titled (*Choice of Law and Waiver of Jury Trial*) in the Security Agreement in the case of the Guarantors, are incorporated herein, *mutatis mutandis*, and shall apply to and govern this Intellectual Property Security Agreement.

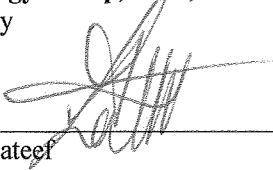
SECTION 5. Conflict Provision. This Intellectual Property Security Agreement has been entered into in conjunction with the provisions of the Security Agreements. The rights and remedies of each party hereto with respect to the security interest granted herein are without prejudice to, and are in addition to those set forth in the Security Agreements, all terms and provisions of which are incorporated herein by reference. In the event that any provisions of this Intellectual Property Security Agreement are in conflict with any Security Agreement, the provisions of such Security Agreement shall govern.

[Signature page follows]

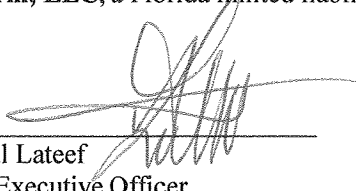
IN WITNESS WHEREOF, each of the undersigned has caused this Intellectual Property Security Agreement to be duly executed and delivered as of the date first above written.

“GRANTORS”

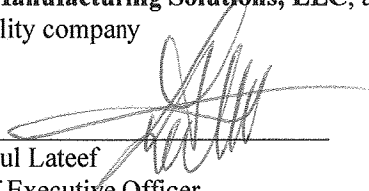
**RAJE Technology Group, LLC**, a Florida limited liability company

By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

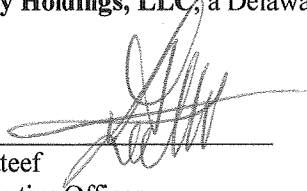
**Plasma-Therm, LLC**, a Florida limited liability company

By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

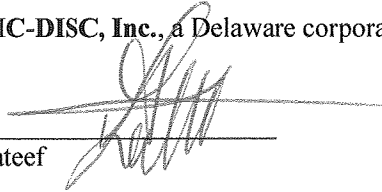
**Rev-Tech Manufacturing Solutions, LLC**, a Florida limited liability company

By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

**Logix Technology Holdings, LLC**, a Delaware limited liability company

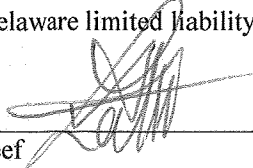
By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

**Plasma-Therm IC-DISC, Inc.**, a Delaware corporation

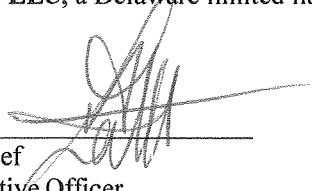
By:   
Name: Abdul Lateef  
Title: President

*[Signatures continue on next page]*

**Drytek, LLC, a Delaware limited liability company**

By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

**Hine Automation, LLC, a Delaware limited liability company**

By:   
Name: Abdul Lateef  
Title: Chief Executive Officer

Intellectual Property Security Agreement

**TRADEMARK**  
**REEL: 005866 FRAME: 0359**

Schedule 1

[See attached]

Intellectual Property Security Agreement

**TRADEMARK**  
**REEL: 005866 FRAME: 0360**



**Schedule 1**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
4	US	Perimeter seal for backside cooling	Kenney	8/3/2004 6,771,482
11	US	Method for Etching Vias	Westerman Johnson	1/25/2005 6,846,747
13	TW	Taiwan filing of (PT-4) Perimeter seal for backside cooling	Kenney	8/21/2003 185678
16	US	Notch-free Etching of High Aspect SOI structures using Alternating Deposition and Etching and Pulsed ICP	Westerman Johnson Lai	6/14/2005 6,905,626
17	US	Sidewall smoothing in high aspect ratio/deep etching using a discrete gas switching method	Westerman Johnson Lai	8/2/2005 6,924,235
19	TW	Taiwan filing of (PT-7) Etching of Photomask Substrates Using Pulsed Plasma	Johnson Constantine Onishi	5/14/2004 195269
21	TW	Taiwan filing of (PT-6) Etching of Thin Damage Sensitive Layers Using High Frequency Pulsed Plasma	Westerman Johnson	5/1/2005 1231955
23	US	End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	1/3/2006 6,982,175
24	US	A Method and Apparatus for Process Control in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai	10/3/2006 7,115,520
26	TW	Taiwan filing of (PT-11) Method for improved etching of GaAs	Westerman Johnson	3/21/2007 1277152
27	US	Etching of Chromium Layers on Photomasks Utilizing High Density Plasma and Low Frequency RF Bias	Constantine Plumhoff Johnson Westerman	3/7/2006 7,008,877
28	US	Envelope Follower End Point Detection in Time Division Multiplexed Processes	Johnson Westerman	09/05/2006 7,101,805
30	TW	Taiwan filing of (PT-16) Notch-free Etching of High Aspect SOI structures using Alternating Deposition and Etching and Pulsed ICP	Westerman Johnson Lai	3/1/2008 1294148
35	TW	Taiwan filing of (PT 17) Sidewall smoothing in high aspect ratio/deep etching using a discrete gas switching method	Westerman Johnson Lai	1/21/2009 1305664
37	EU	EU filing of (PT-4) Perimeter seal for backside cooling	Kenney	Nationalized in Germany, Switzerland and France
39	TW	Taiwan filing of (PT-23) End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	11/21/2009 1317539

**Exhibit A**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
40	TW	Taiwan filing of (PT-24) A Method and Apparatus for Process Control in TDM Etch Processes	Westerman Johnson Lai	11/21/2009 1317537
42	TW	Taiwan filing of (PT-28) Envelope Follower End Point Detection in Time Division Multiplexed Processes	Johnson Westerman	1/1/2010 1319207
44	TW	Taiwan filing of (PT-27) Etching of Chromium Layers on Photomasks Utilizing High Density Plasma and Low Frequency RF Bias	Constantine Plumhoff Johnson Westerman	02/21/2010 1320947
50	US	A Method and Apparatus for Reducing Aspect Ratio Dependent Etching in TDM Etch Processes	Westerman Johnson Lai	06/14/2011 7,959,819
54	US	Method and Apparatus to Improve Plasma Etch Uniformity	Westerman Johnson	05/11/2010 7,713,432
56	CN	China filing of (PT-11) Method for improved etching of GaAs	Westerman Johnson	10/24/2007 100345259C
57	JP	Japan filing of (PT-11) Method for improved etching of GaAs	Westerman Johnson	9/10/2010 4584592
59	TW	Taiwan filing of (PT-36) Notch-Free Etching of High Aspect SOI Structures Using a Time Division Multiplex Process and RF Bias Modulation	Srinivasan Westerman Johnson	12/21/2009 1318780
63	EU	EU filing of (PT-16) Notch-free Etching of High Aspect SOI structures using Alternating Deposition and Etching and Pulsed ICP	Westerman Johnson Lai	Nationalized in Germany, Switzerland and France
65	CN	China filing of (PT-16) Notch-free Etching of High Aspect SOI structures using Alternating Deposition and Etching and Pulsed ICP	Westerman Johnson Lai	5/28/2008 100390925C
67	CN	China filing of (PT-17) Sidewall smoothing in high aspect ratio/deep etching using a discrete gas switching method	Westerman Johnson Lai	8/6/2008 100409414C
69	US	Method for Process Change Detection	Plumhoff	12/1/2009 7,625,824
70	EU	EU filing of (PT-23) End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	Nationalized in Germany, Switzerland and France
71	CN	China filing of (PT-23) End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	11/03/2010 1739185
72	JP	Japan filing of (PT-23) End Point Detection in Time Division Multiplexed Etch Processes	Westerman Johnson	04/22/2011 4724795

**Exhibit A**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
73	US	CIP of (PT-24) A Method and Apparatus for Process Control in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai Teixeira	6/3/2008 7,381,650
74	TW	Taiwan filing of (PT-54) Method and Apparatus to Improve Plasma Etch Uniformity	Westerman Johnson	08/11/2012 I370490
75	TW	Taiwan filing of (PT-50) A Method and Apparatus for Reducing Aspect Ratio Dependent Etching in TDM Etch Processes	Westerman Johnson Lai	06/11/2010 1326112
79	TW	Taiwan filing of (PT-73) A Method and Apparatus for Process Control in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai Teixeira	04/11/2010 1323395
80	US	Optical Emission Interferometry for PECVD using a Gas Injection Hole	Johnson	11/16/2010 7,833,381
82	EU	EU filing of matter 24	Westerman Johnson Lai	Nationalized in Germany
84	CN	China filing of (PT-24) A Method and Apparatus for Process Control in TDM Etch Processes	Westerman Johnson Lai	4/16/2008 100382249C
87	CN	China filing of (PT-28) Envelope Follower End Point Detection in TDM Processes	Johnson Westerman	7/9/2008 100401491C
88	EU	EU filing of (PT-28) Envelope Follower End Point Detection in TDM Processes	Johnson Westerman	Nationalized in Germany, Switzerland
92	US	Improved Method for Etching Photolithographic Substrates	Plumhoff	07/06/2010 7,749,400
100	CN	China filing of (PT-36) Notch-Free Etching of High Aspect SOI Structures Using a Time Division Multiplex Process and RF Bias Modulation	Srinivasan Westerman Johnson	5/27/2009 100490598C
101	EU	EU filing of (PT-36) Notch-Free Etching of High Aspect SOI Structures Using a Time Division Multiplex Process and RF Bias Modulation	Srinivasan Westerman Johnson	Nationalized in Germany, Switzerland and France
103	TW	Taiwan filing of (PT-69) Method for Process Change Detection	Plumhoff	03/01/2011 I338321
105	US	Temperature Control Method for Photolithographic Substrate	Plumhoff Ryan Nolan Johnson Westerman	01/11/2011 7,867,403

**Exhibit A**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
107	TW	Taiwan filing of (PT-81) CIP of (PT-28) Selection of Wavelengths for End Point in a Time Division Multiplexed Process	Johnson Westerman	01/11/2012 I356443
108	US	A Method and Apparatus for Plasma Etching of Positively Sloped Structures	Lai Mackenzie Johnson	11/09/2010 7,829,465
110	TW	Taiwan filing of (PT-80) Optical Emission Interferometry for PECVD using a Gas Injection Hole	Johnson	04/11/2011 I340179
111	US	Method to Minimize CD Etch Bias	Plumhoff Srinivasan Johnson Westerman	05/29/2012 8,187,483
112	EU	EU filing of (PT-50) A Method and Apparatus for Reducing Aspect Ratio Dependent Etching in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai	Nationalized in UK, Germany, Switzerland and France
113	CN	China filing of (PT-50) A Method and Apparatus for Reducing Aspect Ratio Dependent Etching in Time Division Multiplexed (TDM) Etch Processes	Westerman Johnson Lai	7/22/2009 100517596C
116	TW	Taiwan filing of (PT-92) Improved Method for Etching Photolithographic Substrates	Plumhoff	03/11/2011 I338921
119	EU	EU filing of (PT-54) Method and Apparatus to Improve Plasma Etch Uniformity	Westerman Johnson	Nationalized in UK, Germany, Switzerland and France
121	TW	Taiwan filing of matter 98	Johnson Lai	06/01/2014 I440123
123	TW	Taiwan filing of (PT-105) Temperature Control Method for Photolithographic Substrate	Plumhoff Ryan Nolan Johnson Westerman	04/21/2012 I362563
125	TW	Taiwan filing of (PT-111) A Method to Minimize CD Etch Bias	Plumhoff Srinivasan Johnson Westerman	01/21/2013 I383244
127	EU	EU filing of (PT-69) Method for Process Change Detection	Plumhoff	Nationalized in UK, Germany, Switzerland and France
128	JP	Japan filing of (PT-69) Method for Process Change Detection	Plumhoff	08/17/2012 5066517

**Exhibit A****PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
129	CN	China filing of (PT-69) Method for Process Change Detection	Plumhoff	10/13/2010 101218550B
131	EU	EU filing of (PT-73) A Method and Apparatus for Process Control in TDM Etch Processes	Westerman Johnson Lai Teixeira	Nationalized in UK, Germany, Switzerland and France
132	CN	China filing of (PT-73) A Method and Apparatus for Process Control in TDM Etch Processes	Westerman Johnson Lai Teixeira	9/16/2009 100541731C
134	CN	China filing of (PT-81) CIP of (PT-28) Selection of Wavelengths for End Point in a Time Division Multiplexed Process	Johnson Westerman	03/23/2011 101248507B
137	CN	China filing of (PT-80) Optical Emission Interferometry for PECVD using a Gas Injection Hole	Johnson	01/26/2011 101243535B
138	EU	EU filing of (PT-80) Optical Emission Interferometry for PECVD using a Gas Injection Hole	Johnson	Nationalized in UK, Germany, Switzerland and France
140	CN	China filing of matter 92	Plumhoff	02/05/2014 101331431B
141	JP	Japan filing of (PT-92) Improved Method for Etching Photolithographic Substrates	Plumhoff	07/13/2012 5036726
144	CN	China filing of (PT-98) Apparatus and Method for Carrying Substrates	Johnson Lai	03/30/2011 101405857B
148	CN	China filing of (PT-105) Temperature Control Method for Photolithographic Substrate	Plumhoff Ryan Nolan Johnson Westerman	03/30/2011 101461031B
152	JP	Japan filing of (PT-111) A Method to Minimize CD Etch Bias	Plumhoff Srinivasan Johnson Westerman	09/06/2013 5355402
153	CN	China filing of (PT-111) A Method to Minimize CD Etch Bias	Plumhoff Srinivasan Johnson Westerman	07/10/2013 101501568B
154	US	Conductive Seal Ring Electrostatic Chuck	Reynolds	03/20/2012 8,139,340
161	EU	European Filing of Magnet Pole Fabrication Process and Device	Kobrin Ostan	Nationalized in UK, Germany and France

**TRADEMARK****REEL: 005866 FRAME: 0365**

**Exhibit A**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
182	US	Method and Apparatus for Plasma Dicing a Semi-conductor Wafer (2 step process)	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	08/12/2014 8,802,545
188	CN	China filing of (PT-154) Conductive Seal Ring Electrostatic Chuck	Reynolds	08/13/2014 102282645B
191	TW	Taiwan filing of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer (2 step process)	CW Johnson DJ Johnson Westerman Martinez Pays-Volard Grivna	04/01/2016 I528433
191.4	TW	Taiwan filing of (PT-197) (ICP Screen) of Method and Apparatus for Plasma Dicing a Semi-conductor Wafer	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	04/01/2016 I528435
193	US	DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer (Dicing on Tape)	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	07/15/2014 8,778,806
194	US	Method for Dicing a Substrate with Back Metal (Water Jet)	Falvo Martinez Pays-Volard Gauldin Westerman	06/14/2016 9,368,404
195	US	DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Cover Ring	CW Johnson DJ Johnson Pays-Volard Martinez Westerman Grivna	08/05/2014 8,796,154
196	US	DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Lift Mechanism	CW Johnson DJ Johnson Martinez Pays-Volard Rich Gauldin Westerman Grivna	07/22/2014 8,785,332
197	US	DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ICP Screen	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	03/17/2015 8,980,764

**TRADEMARK**

**REEL: 005866 FRAME: 0366**

**Exhibit A****PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
198	US	DIV of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ESC	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	12/01/2015 9,202,720
199	US	CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Tape Under Tension & Multiple Wafer	Gauldin CW Johnson DJ Johnson Martinez Pays-Volard Westerman Grivna	02/03/2015 8,946,058
201	US	CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - large area ESC Details with cover ring	Martinez Pays-Volard CW Johnson DJ Johnson Westerman Grivna	06/30/2015 9,070,760
205	US	DIV of (PT-201) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - ICP screen details	Pays-Volard Martinez CW Johnson DJ Johnson Westerman Grivna	08/11/2015 9,105,705
206	US	CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Perforated Cover Ring, Multi-Wafer Cover Ring & PCM Fills	Geerpuram Pays-Volard Martinez CW Johnson DJ Johnson Westerman	04/08/2014 8,691,702
210	US	CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Double Scribe Line	Lazerand Pays-Volard Martinez CW Johnson Westerman Grivna	05/17/2016 9,343,365
214	US	DIV of (PT-206) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Perforated Cover Ring, Multi-Wafer Cover Ring & PCM Fills	Geerpuram Pays-Volard Martinez CW Johnson DJ Johnson Westerman	12/01/2015 9,202,721

**Exhibit A**

**PATENTS**

<b>PT Ref #</b>		<b>Title</b>	<b>Inventors</b>	<b>Issue Date Issue No.</b>
215	TW	Taiwan Filing of (PT 199) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - Tape Under Tension & Multiple Wafer	Gauldin CW Johnson DJ Johnson Martinez Pays-Volard Westerman Grivna	03/21/2016 1527108
217	US	CIP of (PT-182) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - intermediate ring with cover ring	Gauldin Geerpuram Mackenzie Lazerand Pays-Volard Martinez Westerman Grivna Doub	07/14/2015 9,082,839
217 DIV	US	DIV of (PT-217) Method and Apparatus for Plasma Dicing a Semi-conductor Wafer - intermediate ring without cover ring	Gauldin Geerpuram Mackenzie Lazerand Pays-Volard Martinez Westerman Grivna Doub	12/01/2015 9,202,737
n/a	US	Etching process for producing substantially undercut free silicon on insulator structures	Donohue Johnson Devre	6/6/2000 6,071,822
n/a	US	Morphed processing of semiconductor devices	Teixeira Devre Dawson Johnson	7/9/2002 6,417,013
n/a	US	Magnetic pole fabrication process and device	Kobrin Ostan	4/1/2003 6,540,928
n/a	US	Embedded attenuated phase shift mask and method of making embedded attenuated phase shift mask	Westerman Constantine	4/8/2003 6,544,696
n/a	US	Magnetic pole fabrication process and device	Kobrin	4/15/2003 6,547,975
n/a	US	Method for thin film lift-off processes using lateral extended etching masks and device	Lishan	8/12/2003 6,605,519



## Trademark Registrations and Applications

Trademark	Owner	Serial No.	Registration No.	Country	Filing Date
SINGULATOR	Plasma-Therm, LLC	85838262	4818288	US	5/6/2013
CORTEX	Plasma-Therm, LLC	85114111	4136245	US	8/23/2010
VERSALINE	Plasma-Therm, LLC	78178079	2893124	US	10/24/2002
SHUTTLELINE	Plasma-Therm, LLC	78178075	2893123	US	10/24/2002
VERSAWORKS	Plasma-Therm, LLC	77926461	3841335	US	2/2/2010
PTI	Plasma-Therm, LLC	77918288	3840760	US	1/22/2010
790+	Plasma-Therm, LLC	77548329	3730528	US	8/15/2008
NEXTRAL	Plasma-Therm, LLC	77856218	3806343	US	10/23/2009
PLASMA-THERM	Plasma-Therm, LLC	77554869	3687253	US	8/25/2008
ENDPOINTWORKS	Plasma-Therm, LLC	77927602	3902954	US	2/3/2010
MASK ETCHER	Plasma-Therm, LLC	77021763	3383876	US	10/16/2006
VERSALOCK	Plasma-Therm, LLC	74614175	2001901	US	12/22/1994
SHUTTLELOCK	Plasma-Therm, LLC	74019457	1625640	US	1/16/1990
Dytek (goods)	Drytek, LLC	85018006	4210502	US	4/20/2010
Dytek (services)	Drytek, LLC	85018001	3994856	US	4/20/2010